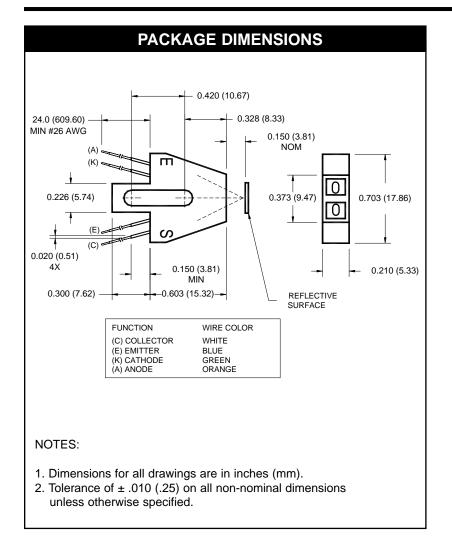
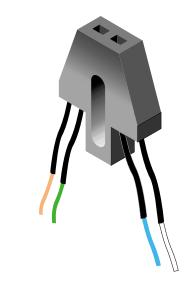
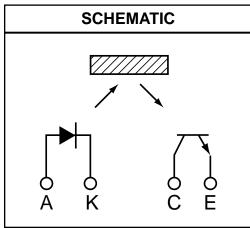


QRC1133







DESCRIPTION

The QRC1133 consists of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.

FEATURES

- Phototransistor output
- · High Sensitivity
- Low cost plastic housing
- #26 AWG, 24 inch PVC wire termination



QRC1133

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Units					
Operating Temperature	T _{OPR}	-40 to +85	°C					
Storage Temperature	T _{STG}	-40 to +85	°C					
Soldering Temperature (Iron)(2,3,4)	T _{SOL-I}	240 for 5 sec	°C					
Soldering Temperature (Flow)(2,3)	T _{SOL-F}	260 for 10 sec	°C					
EMITTER								
Continuous Forward Current	l _F	50	mA					
Reverse Voltage	V _R	5	V					
Power Dissipation(1)	PD	100	mW					
SENSOR								
Collector-Emitter Voltage	V _{CEO}	30	V					
Emitter-Collector Voltage	V _{ECO}	5	V					
Collector Current	I _C	20	mA					
Power Dissipation ⁽¹⁾	P _D	100	mW					

NOTES

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6mm) minimum from housing.
- 5. D is the distance from the assembly face to the reflective surface.
- 6. Cross talk is the photo current measured with current to the input diode and no reflecting surface.
- 7. Measured using an Eastman Kodak neutral test card with 90% diffused reflecting surface.

ELECTRICAL / OPTICAL CHARACTERISTICS (T _A = 25°C)									
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS			
EMITTER		V _F	_	_	1.7	V			
Forward Voltage	$I_F = 40 \text{ mA}$								
Reverse Current	V _R = 2.0 V	I _R	_	_	100	μA			
Peak Emission Wavelength	I _F = 20 mA	λ_{PE}	_	940	_	nm			
SENSOR		BV _{CEO}	30	_	_	V			
Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}$								
Emitter-Collector Breakdown Voltage	I _E = 0.1 mA	BV _{ECO}	5	_	_	V			
Collector-Emitter Dark Current	$V_{CE} = 10 \text{ V}, I_{F} = 0 \text{ mA}$	I _{CEO}	_	_	100	nA			
COUPLED	1 40mA V EV D 1E0#(5.6)	I _{C(ON)}	0.20	_	_	mA			
On-state Collector Current	$I_F = 40 \text{mA}, V_{CE} = 5 \text{V}, D = .150''^{(5,6)}$								
Collector-Emitter	$I_F = 40 \text{ mA}, I_C = 0.1 \text{ mA}$	V _{CE (SAT)}			0.4	V			
Saturation Voltage	D = 1.50" ^(5,7)								
Rise Time	V_{CE} = 5 V, R_L = 100 Ω	t _r	_	8	_	μs			
Fall Time	$I_{C(ON)} = 5 \text{ mA}$	t _f	_	8	_	μο			
Crosstalk	$I_F = 40 \text{ mA}, V_{CE} = 5 \text{ V}^{(7)}$	I _{CX}	_	_	1.00	μΑ			



QRC1133

TYPICAL PERFORMANCE CURVES

Fig. 1 Forward Voltage vs. Forward Current 1.60 1.40 VF - FORWARD VOLTAGE (V) 1.20 1.00 0.80 0.60 0.40 0.20 0.1 1.0 10 100 IF - FORWARD CURRENT (mA)

Fig. 2 Normalized Collector Current vs. Forward Current 10.0 IC - COLLECTOR CURRENT (mA) 1.00 0.10 0.01 $V_{CE} = 5 V$ D = .05'.001 0.0 10 20 30 40 IF - FORWARD CURRENT (mA)

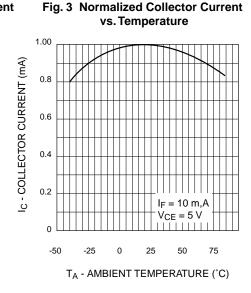


Fig. 4 Normalized Collector Dark **Current vs. Temperature** 10² I_{CEO} - COLLECTOR DARK CURRENT 10¹ V_{CE} = 10 V 10 1.0 10⁻¹ 10-2 10-3 50 -25 0 25 50 75 100 TA - AMBIENT TEMPERATURE (°C)

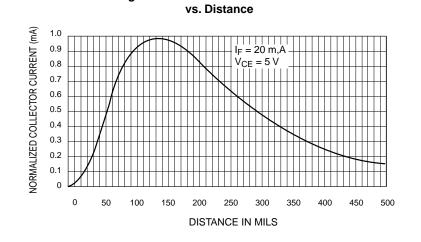


Fig. 5 Normalized Collector Current



QRC1133

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body,or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.